

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- General purpose switching and amplification, e.g. telephony and professional communication equipment.

DESCRIPTION

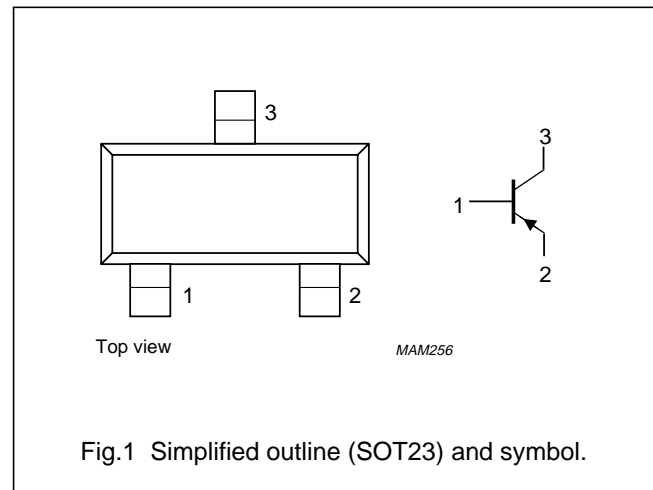
PNP transistor in a SOT23 plastic package.
NPN complement: PMBS3904.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBS3906	*O6

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	–40	V
V _{CEO}	collector-emitter voltage	open base	–	–40	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–100	mA
I _{CM}	peak collector current		–	–200	mA
I _{BM}	peak base current		–	–200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–50	nA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -1\text{ V}$; (see Fig.2) $I_C = -0.1\text{ mA}$ $I_C = -1\text{ mA}$ $I_C = -10\text{ mA}$ $I_C = -50\text{ mA}$; note 1 $I_C = -100\text{ mA}$; note 1	60 80 100 60 30	– – 300 – –	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$ $I_C = -50\text{ mA}; I_B = -5\text{ mA}$; note 1	– –	–250 –400	mV mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$ $I_C = -50\text{ mA}; I_B = -5\text{ mA}$; note 1	– –	–850 –950	mV mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = -5\text{ V}; f = 100\text{ MHz}$	–	4.5	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = -0.5\text{ V}; f = 100\text{ MHz}$	–	12	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -20\text{ V}; f = 100\text{ MHz}$	150	–	MHz
F	noise figure	$I_C = -100\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 1\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz};$	–	4	dB

Switching times (between 10% and 90% levels); (see Fig.3)

t_{on}	turn-on time	$I_{Con} = -10\text{ mA}; I_{Bon} = -1\text{ mA};$ $I_{Boff} = 1\text{ mA}$	–	100	ns
t_d	delay time		–	50	ns
t_r	rise time		–	50	ns
t_{off}	turn-off time		–	700	ns
t_s	storage time		–	600	ns
t_f	fall time		–	100	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.